L Number	Hits	Search Text	DB	Time stamp
-	9503	trench with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:50
-	2128	hemispherical with grain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:51
-	103	(trench with nitride) and (hemispherical with grain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:51
-	547	etch$3 with HSG	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:51
-	86	438/FOR.100.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:51
-	587	438/243.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	146	438/246.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	111	438/249.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	510	438/386.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	91	438/389.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	680	438/255.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	727	438/398.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	261	438/964.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	61	438/FOR.220.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:51
-	262	438/558.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	1482515	plate electrode	USPAT; US-PGPUB	2004/08/03 12:51
-	245	438/563.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	316262	diffusion diffus$3	USPAT; US-PGPUB	2004/08/03 12:51
-	1075566	glass oxide	USPAT; US-PGPUB	2004/08/03 12:51
-	273051	capacitor	USPAT; US-PGPUB	2004/08/03 12:51
-	474414	trench recess	USPAT; US-PGPUB	2004/08/03 12:51
-	2103	hsg	USPAT; US-PGPUB	2004/08/03 12:51

-	7297	(plate electrode) with (diffusion diffus$3) with (glass oxide)	USPAT; US-PGPUB	2004/08/03 12:51
-	71	((trench with nitride) and (hemispherical with grain) and capacitor) not ((trench with nitride) same (hemispherical with grain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:51
-	18	(trench with nitride) same (hemispherical with grain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:51
-	85	((trench with nitride) and (hemispherical with grain)) not ((trench with nitride) same (hemispherical with grain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:51
-	509	(etch$3 with HSG) and (capacitor node plate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:51
-	39	148/DIG.138.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:51
-	54	438/FOR.488.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:51
-	85	438/392.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	116	438/923.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	35	((plate electrode) with (diffusion diffus$3) with (glass oxide)) and capacitor and (trench recess) and hsg	USPAT; US-PGPUB	2004/08/03 12:51
-	87	(trench with nitride) and (hemispherical with grain) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:57
-	83	((trench with nitride) and (hemispherical with grain) and capacitor) not (@ad>20030423 @rlad>20030423)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:58
-	3387	"doped oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:50
-	0	(NH4OH with etchant) same "doped oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:51
-	0	(NH4OH with etchant) and "doped oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:51

-	5	(NH4OH with etchant) same oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:51
-	62	NH4OH with etchant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:58
-	370685	@ad>20030423 @rlad>20030423	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:59
-	60	(NH4OH with etchant) not (@ad>20030423 @rlad>20030423)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 13:56
-	1	6306724.pn.	USPAT	2004/08/04 14:02
-	1	5911109.pn.	USPAT	2004/08/04 15:39
-	1	6242323.pn.	USPAT	2004/08/04 15:55
-	173	recess with "pad oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 15:56
-	9	(recess with "pad oxide") same capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 15:56